

Nisha Chugh

List of Publications by Year in descending order

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8
papers

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2258059

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34
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#	ARTICLE	IF	CITATIONS
1	Sheet carrier concentration and current-voltage analysis of Al _{0.15} Ga _{0.85} N/GaN/Al _{0.15} Ga _{0.85} N double heterostructure hemt incorporating the effect of traps. <i>Microsystem Technologies</i> , 2022, 28, 665-674.	2.0	8
2	Extraction of admittance parameters of symmetrically doped AlGa _N /Ga _N /AlGa _N DH-HEMT for microwave frequency applications. <i>Microsystem Technologies</i> , 2021, 27, 4065-4072.	2.0	4
3	Analysis of Al _{0.15} Ga _{0.85} N/GaN/Al _{0.15} Ga _{0.85} N DH-HEMT for RF and Microwave Frequency Applications. <i>Semiconductors</i> , 2019, 53, 1784-1791.	0.5	5
4	Impact of Donor Layer Thickness, Doping Concentration and Gate-Width on Gate-Capacitance of AlGa _N /Ga _N Single and Double Heterostructure HEMT for Microwave Frequency Applications. , 2018, , .		1
5	Impact of donor-layer doping & thickness, gate-length and temperature on potential and electron concentration in AlGa _N /Ga _N Double-Heterostructure and Single-Heterostructure HEMT. , 2018, , .		0
6	Polarization dependent charge control model for microwave performance assessment of AlGa _N /Ga _N /AlGa _N double heterostructure HEMTs. <i>Journal of Computational Electronics</i> , 2018, 17, 1229-1240.	2.5	12
7	Sheet carrier concentration and threshold voltage modeling of asymmetrically doped AlGa _N /Ga _N /AlGa _N double heterostructure HEMT. , 2017, , .		7
8	Applicability of Field Plate in Double Channel GaN HEMT for Radio-Frequency and Power-Electronic Applications. <i>Silicon</i> , 0, , 1.	3.3	8